

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:

Varun Singh, et al.

Serial No.: Not Assigned

Filed: Herewith

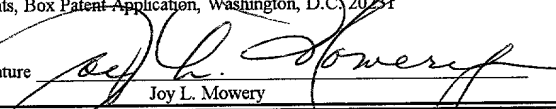
§
§
§
§
§
§

Previous Examiner: H. Tsai

Previous Group Art Unit: 2812

For: AN IMPROVED POLYSILICON RESISTOR HAVING ADJUSTABLE
TEMPERATURE COEFFICIENTS AND THE METHOD OF MAKING THE
SAME

BOX: Patent Application
Assistant Commissioner For Patents
Washington, D.C. 20231

CERTIFICATE OF MAILING BY EXPRESS MAIL	
"EXPRESS MAIL" Mailing Label No.: EL749031617US	
Date of Deposit:	9/26/01
I hereby certify that this paper or fee is being deposited with the U.S. Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to the Assistant Commissioner for Patents, Box Patent Application, Washington, D.C. 20231	
Signature	
	Joy L. Mowery

Dear Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above-identified application, please amend this application as follows:

IN THE CLAIMS

Please cancel Claims 3-10 and 13-15. Claims 1-2 and 11-12 remain for consideration in this application.

1. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from $\sim 6 \times 10^{19} \text{ cm}^{-3}$ to $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

2. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

11. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than $\sim 6 \times 10^{19} \text{ cm}^{-3}$.

12. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique.

REMARKS

In view of the above, it is believed that this application is in condition for allowance, and such a Notice is respectfully requested.

Respectfully submitted,

JENKENS & GILCHRIST
A Professional Corporation



Stuart D. Dwork
Reg. No. 31,103

1445 Ross Avenue, Suite 3200
Dallas, Texas 75202-2799
214/855-4727
214/855-4300 (fax)

20661-801D1-26749560